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# N-Channel 240 V (D-S) MOSFET

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)(Typ.)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)	
240	7.7 at V <sub>GS</sub> = 10 V	0.11	2.1 nC	
240	9.07 at V <sub>GS</sub> = 4.5 V			

#### **FEATURES**

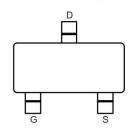
- · DT-Trench Power MOSFET
- 100 % R<sub>g</sub> and UIS Tested



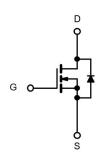
### **APPLICATIONS**

- · Power Management for Portable and Consumer
  - Load Switches
  - DC/DC Converters





Top View



N-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T <sub>J</sub> = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	LIMIT	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	240	V	
Gate-Source Voltage		V <sub>GS</sub>	± 20		
Continuous Drain Current (T, = 150 °C)	T <sub>A</sub> = 25 °C	T.	0.11		
Continuous Drain Current (1) = 130 °C)	T <sub>A</sub> = 70 °C	- I <sub>D</sub>	0.09	A	
Pulsed Drain Current		I <sub>DM</sub>	0.4	A	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	0.36	W	
	T <sub>A</sub> = 70 °C		0.23	•	
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C	

THERMAL RESISTANCE RATINGS			
PARAMETER	SYMBOL	LIMIT	UNIT
Junction-to-Ambient (PCB Mount) <sup>b</sup>	R <sub>thJA</sub>	347	°C/W

#### Notes:

a.  $T_C = 25$  °C.

b. Surface mounted on 1" x 1" FR4 board.

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PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static						•	
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	240	-	-	V	
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \mu A$	0.8	-	1.8	] v	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$	-		± 10	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 240 V, V <sub>GS</sub> = 0 V	-	-	1	μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	0.1	-	-	Α	
Drain-Source On-State Resistance <sup>a</sup>	В	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.1 A	-	7.7	14	Ω	
	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 0.09 \text{ A}$	-	9.07	20		
Forward Transconductance a	9 <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 0.08 A	-	0.13	-	S	
Dynamic <sup>b</sup>							
Input Capacitance	C <sub>iss</sub>		-	58	1-	pF	
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 25 \text{ V}, f = 1 \text{MHz}$	-	7.3	-		
Reverse Transfer Capacitance	C <sub>rss</sub>		-	2.8	-		
Total Gate Charge <sup>c</sup>	Qg		-	2.1	-	nC	
Gate-Source Charge <sup>c</sup>	Q <sub>gs</sub>	$V_{DS} = 192 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 0.1 \text{ A}$	-	0.16	-		
Gate-Drain Charge <sup>c</sup>	Q <sub>gd</sub>		-	0.8	-		
Gate Resistance	$R_{g}$	f = 1 MHz	-	2.4	-	Ω	
Turn-On Delay Time	t <sub>d(on)</sub>			3.3			
Rise Time	t <sub>r</sub>	$V_{DD} = 120 \text{ V}, I_D = 0.1 \text{ A},$		3.1		ns	
Turn-Off DelayTime	t <sub>d(off)</sub>	$V_{GS} = 10 \text{ V}, R_g = 6 \Omega$		13.7			
Fall Time	t <sub>f</sub>			64.5			
Drain-Source Body Diode Ratings an	d Characteri	stics <sup>b</sup> (T <sub>C</sub> = 25 °C)					
Continuous Source Current	Is	T <sub>C</sub> = 25 °C	-	-	0.11	Α	
Pulsed Source Current	I <sub>SM</sub>		-	-	0.4	Α	
Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 0.1 A, V <sub>GS</sub> = 0 V	-	-	1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>	I= 0.1 A,dI/dt = 100 A/µs, T = 25 °C		42.9		ns	
dy Diode Reverse Recovery Charge   Q <sub>rr</sub>   1- 0.1 A,αl/dt = 100 A/μs, 1 - 25 C			22.6		nC		

#### Notes

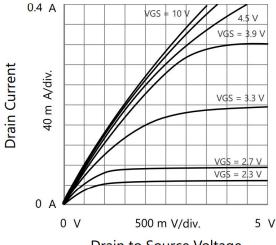
- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

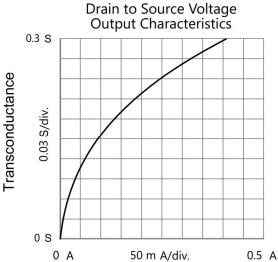
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

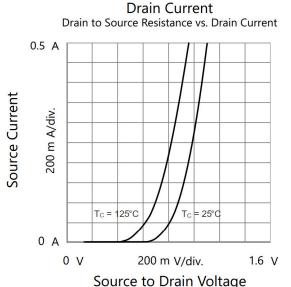




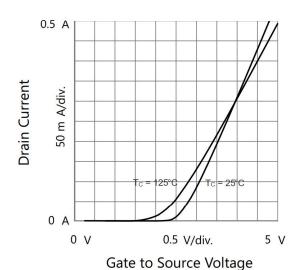
#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

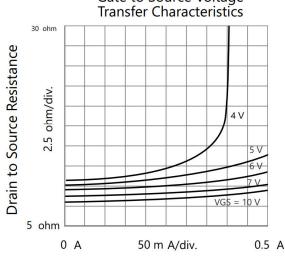


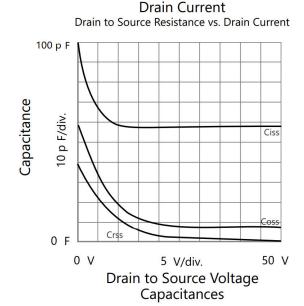




**Body Diode Forward Characteristics** 

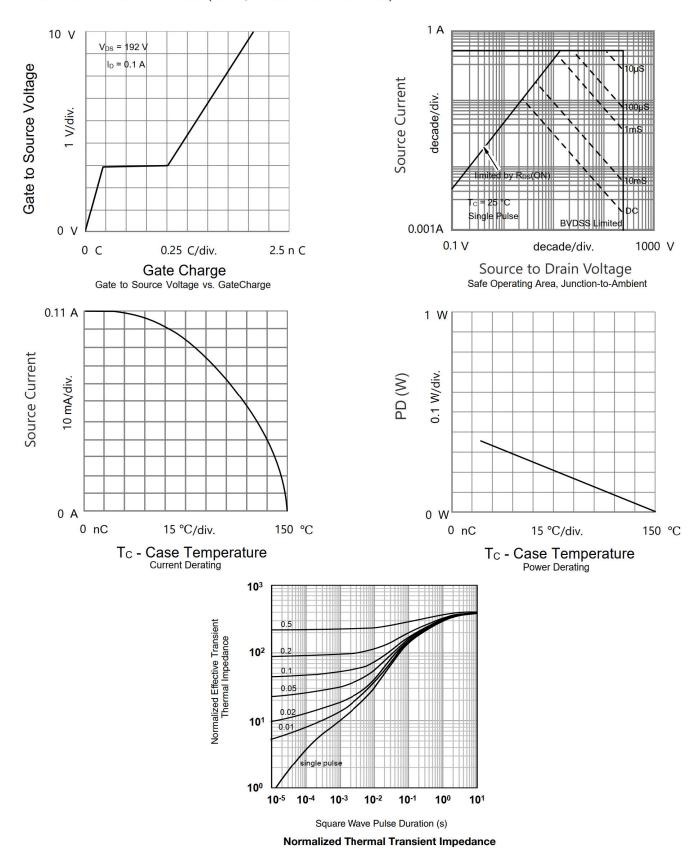








#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)







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